# **NCE N-Channel Super Trench Power MOSFET**

#### **Description**

The series of devices uses **Super Trench** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{DS(ON)}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

#### **Application**

- DC/DC Converter
- •Ideal for high-frequency switching and synchronous rectification

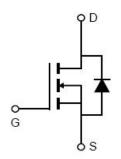
#### **General Features**

- $V_{DS}$  =60V, $I_D$  =90A  $R_{DS(ON)}$ =6.4m $\Omega$  , typical@  $V_{GS}$ =10V
- Excellent gate charge x R<sub>DS(on)</sub> product(FOM)
- Very low on-resistance R<sub>DS(on)</sub>
- 175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!

**TO-263** 





**Schematic Diagram** 

### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP6090D	NCEP6090D	TO-263-2L	Ø330mm	24 mm	800 units

#### Absolute Maximum Ratings (T<sub>c</sub>=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	60	V
Gate-Source Voltage	V <sub>G</sub> s	±20	V
Drain Current-Continuous	I <sub>D</sub>	90	Α
Drain Current-Continuous(T <sub>C</sub> =100 ℃)	I <sub>D</sub> (100℃)	63.6	Α
Pulsed Drain Current	I <sub>DM</sub>	360	Α
Maximum Power Dissipation	P <sub>D</sub>	100	W
Derating factor		0.67	W/℃
Single pulse avalanche energy (Note 1)	E <sub>AS</sub>	320	mJ
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 175	$^{\circ}$ C

#### **Thermal Characteristic**

Thermal Resistance, Junction-to-Case	R <sub>eJC</sub>	1.50	°C/W

# Electrical Characteristics (T<sub>C</sub>=25 ℃ unless otherwise noted)

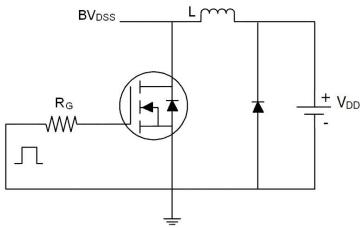
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics			•			
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250µA	60		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V,V <sub>GS</sub> =0V	-	-	1	μΑ
Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{GS}$ =±20 $V$ , $V_{DS}$ =0 $V$	-	-	±100	nA
On Characteristics						
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS}=V_{GS},I_{D}=250\mu A$	2	3	4	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =45A	-	6.4	7.2	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =5V,I <sub>D</sub> =45A	-	35	-	S
Dynamic Characteristics						
Input Capacitance	C <sub>lss</sub>	V <sub>DS</sub> =30V,V <sub>GS</sub> =0V,	-	1700	-	PF
Output Capacitance	Coss		-	345	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0MHz	-	8	-	PF
Switching Characteristics (Note 2)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	8	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =30 $V$ , $I_{D}$ =45 $A$	-	2	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =10V, $R_{G}$ =4.7 $\Omega$	-	29	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	4	-	nS
Total Gate Charge	Qg	V <sub>DS</sub> =30V,I <sub>D</sub> =45A,	-	26.9		nC
Gate-Source Charge	Q <sub>gs</sub>		-	9.4		nC
Gate-Drain Charge	Q <sub>gd</sub>	V <sub>GS</sub> =10V	-	4.6		nC
Drain-Source Diode Characteristics			•			
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =45A	-		1.2	V
Diode Forward Current	Is		-	-	90	Α
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> = I <sub>S</sub>	-	38		nS
Reverse Recovery Charge	Qrr	di/dt = 100A/μs	-	48		nC

#### Notes:

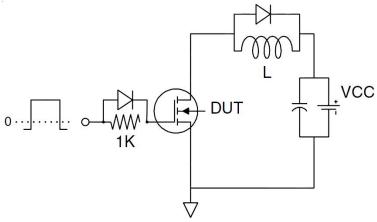
- 1. EAS condition : Tj=25  $^{\circ}\text{C}$  ,VDD=30V,VG=10V,L=0.5mH,Rg=25 $\Omega$
- 2. Guaranteed by design, not subject to production
- 3. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of TJ(MAX)=175° C. The SOA curve provides a single pulse rating.

## **Test Circuit**

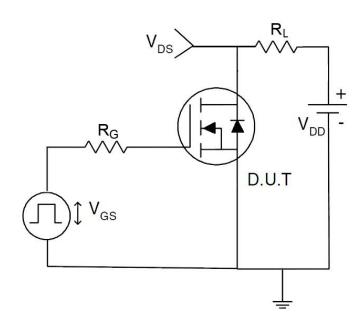
# 1) E<sub>AS</sub> test Circuit



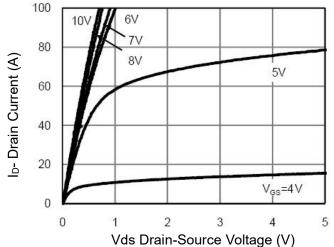
# 2) Gate charge test Circuit



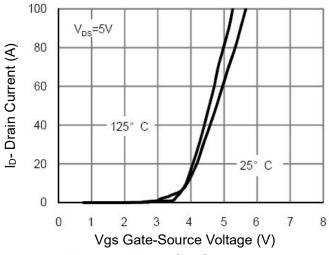
# 3) Switch Time Test Circuit







**Figure 1 Output Characteristics** 



**Figure 2 Transfer Characteristics** 

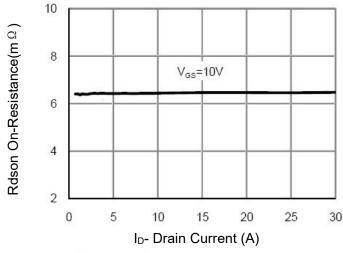


Figure 3 Rdson- Drain Current

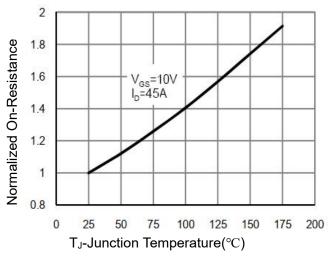


Figure 4 Rdson-JunctionTemperature

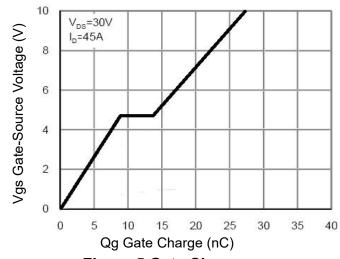


Figure 5 Gate Charge

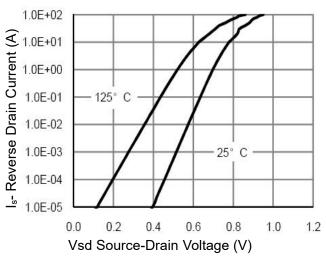
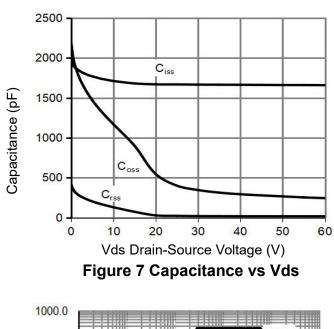
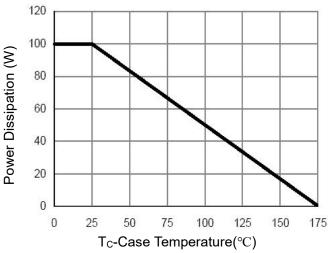
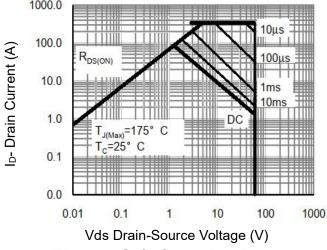


Figure 6 Source- Drain Diode Forward









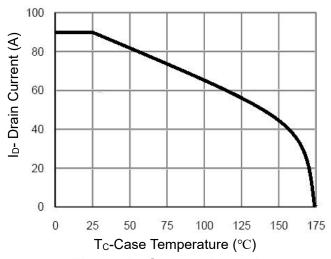


Figure 8 Safe Operation Area(Note3)

Figure 10 Current De-rating

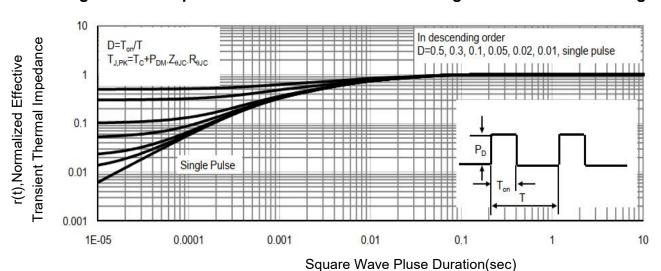
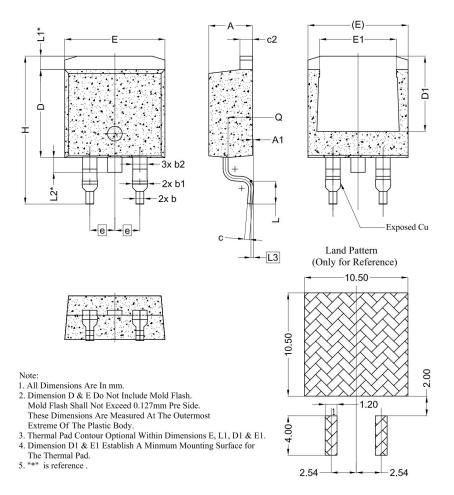


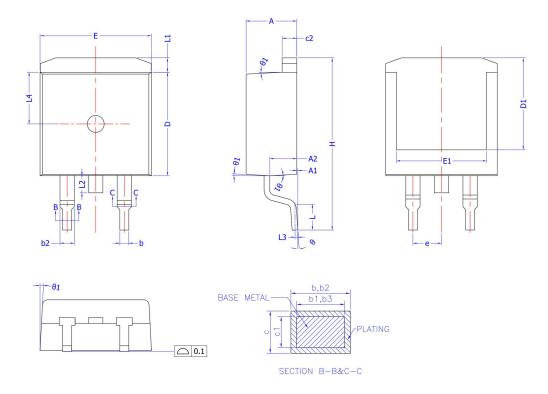
Figure 11 Normalized Maximum Transient Thermal Impedance

# TO-263-2L(G) Package Information



SYMBOL	DIMENSIONS				
	MIN.	NOM.	MAX.		
Α	4.24	4.44	4.64		
A1	0.00	0.10	0.25		
b	0.70	0.80	0.90		
b1	1.20	1.55	1.75		
b2	1.20	1.45	1.70		
С	0.40	0.50	0.60		
c2	1.15	1.27	1.40		
D	8.82	8.92	9.02		
D1	6.86	7.65	-		
E	9.96	10.16	10.36		
E1	6.89	7.77	7.89		
е	2.54 BSC				
н	14.61	15.00	15.88		
Г	1.78	2.32	2.79		
L1	1.36 REF.				
L2	1.50 REF.				
L3	0.25 BSC				
Q	2.30	2.48	2.70		

# TO-263-2L(P) Package Information



# COMMON DIMENSIONS (UNITS OF MEASURE =MILLIMETER)

SYMBOL	MIN	NOM	MAX	
Α	4.40	4.50	4.60	
A1	0	0.10	0.25	
A2	2.20	2.40	2.60	
b	0.76		0.89	
b1	0.75	0.80	0.85	
b2	1.23		1.37	
b3	1.22	1.27	1.32	
С	0.47		0.60	
c1	0.46	0.51	0.56	
c2	1.25	1.30	1.35	
D	9.10	9.20	9.30	
D1	8.00			
E	9.80	9.90	10.00	
E1	7.80			
e	2.54 BSC			
H	14.90	15.30	15.70	
L	2.00	2.30	2.60	
L1	1.17	1.27	1.40	
L2			1.75	
L3	0.25BSC			
L4	4.60 REF			
θ	0°	1	8°	
θ1	1°	3°	5°	

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